

Very low capacitance bidirectional ESD protection diodes17 August 2015Product data sheet

1. General description

Two bidirectional ElectroStatic Discharge (ESD) protection diodes designed to protect two signal lines from damage caused by ESD and other transients. The device is housed in a DFN1006B-3 (SOT883B) leadless ultra small Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Bidirectional ESD protection of two lines
- Ultra small SMD plastic package
- ESD protection up to 30 kV; IEC 61000-4-2
- I_{PPM} = 9 A; IEC 61000-4-5 (surge)
- Ultra low leakage current: I_{RM} = 1 nA
- AEC-Q101 qualified

3. Applications

- Computers and peripherals
- Audio and video equipment
- Cellular handsets and accessories
- Communication systems
- Portable electronics

4. Quick reference data

Table 1. Qui	ick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RWM}	reverse standoff voltage	T _{amb} = 25 °C	-	-	5	V
C _d	diode capacitance	f = 1 MHz; V_R = 0 V; T_{amb} = 25 °C	-	18	20	pF





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5. Pinning information

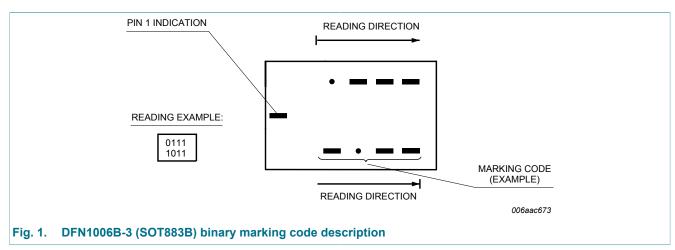
Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K1	cathode	1	
2	K2	cathode	2	
3	К3	common cathode	Transparent top view DFN1006B-3 (SOT883B)	006aab331

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PESD5V0V2BMB	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PESD5V0V2BMB	00 11 01 00



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8. Limiting values

Table 5. Limiting values

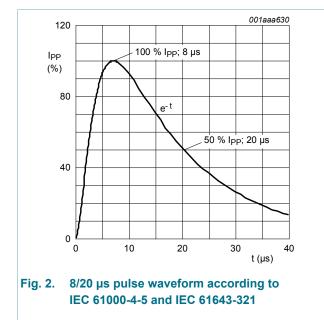
In accordance with the Absolute Maximum Rating System (IEC 60134).

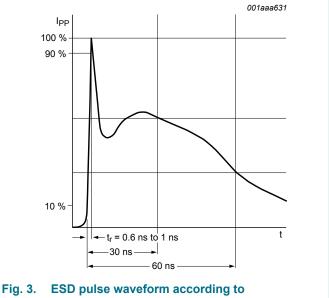
Symbol	Parameter	Conditions		Min	Мах	Unit
I _{PPM}	rated peak pulse current	t _p = 8/20 μs	[1][2]	-	9	А
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
ESD maxim	um ratings		I			
V _{ESD}	electrostatic discharge voltage	IEC 61000-4-2; contact discharge	[1][3]	-	30	kV
		IEC 61000-4-2; air discharge	[1][3]	-	30	kV
		MIL-STD-883; human body model	[1]	-	10	kV

[1] Measured from pin 1 or 2 to pin 3.

[2] According to IEC 61000-4-5 and IEC 61643-321.

[3] Device stressed with ten non-repetitive ESD pulses.





IEC 61000-4-2

9. Characteristics

Table 6. Ch	aracteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RWM}	reverse standoff voltage	T _{amb} = 25 °C		-	-	5	V
I _{RM}	reverse leakage current	V _{RWM} = 5 V; T _{amb} = 25 °C	[1]	-	1	10	nA
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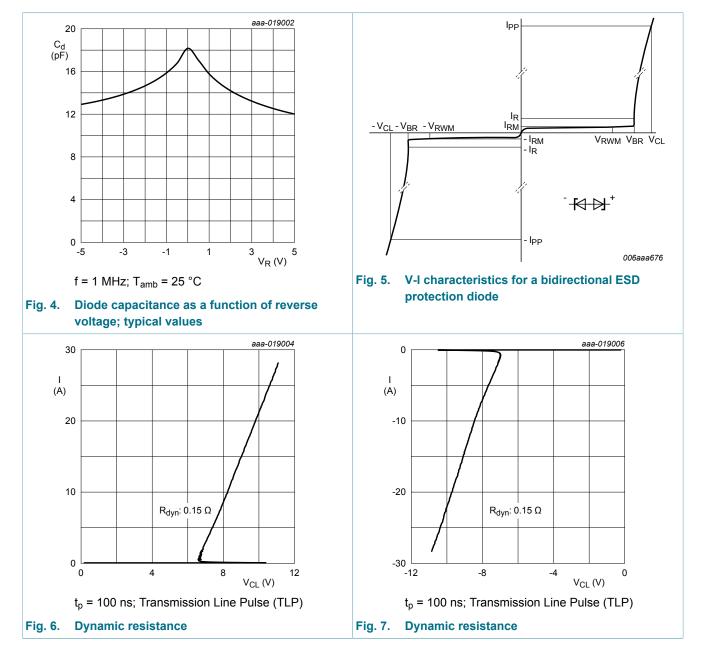
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{BR}	breakdown voltage	I _R = 5 mA; T _{amb} = 25 °C	[1]	5.5	6.8	7.8	V
C _d	diode capacitance	f = 1 MHz; V _R = 0 V; T _{amb} = 25 °C		-	18	20	pF
V _{CL}	clamping voltage	I_{PP} = 1 A; T_{amb} = 25 °C; t_p = 8/20 µs	[1][2]	-	8	9.5	V
		I_{PPM} = 9 A; T_{amb} = 25 °C; t_p = 8/20 µs	[1][2]	-	11	12.5	V
R _{dyn}	dynamic resistance	I _R = 10 A; T _{amb} = 25 °C	[1][3]	-	0.15	-	Ω

[1] Measured from pin 1 or 2 to pin 3.

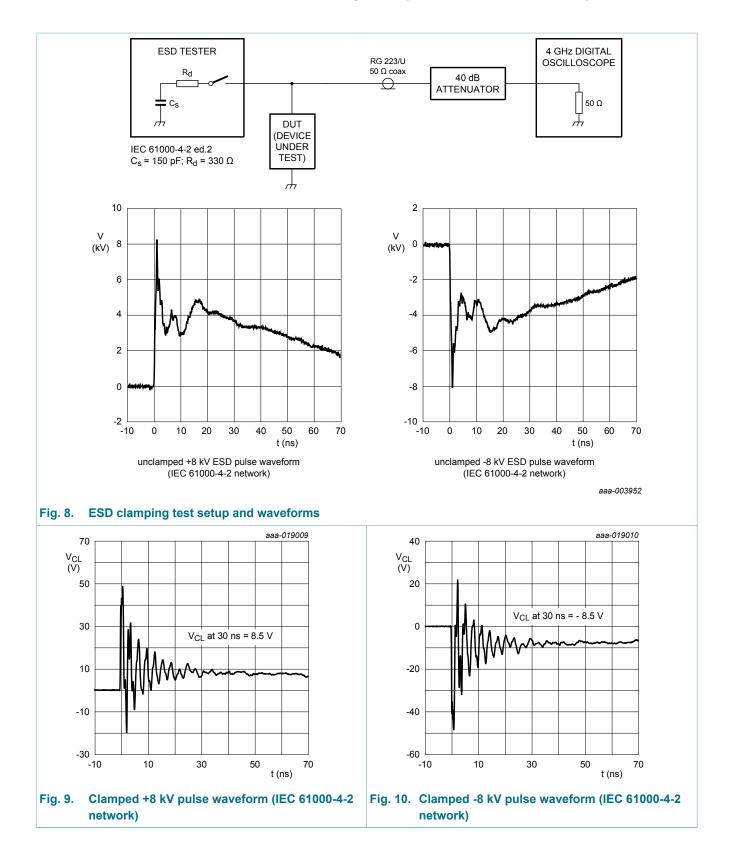
- [2] According to IEC 61000-4-5 and IEC 61643-321.
- [3] Non-repetitive current pulse, Transmission Line Pulse (TLP) t_p = 100 ns; square pulse; ANSI / ESD STM5.5.1-2008.



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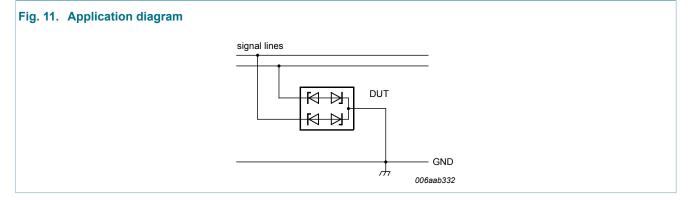
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10. Application information

The device is designed for the protection of up to two bidirectional data lines from surge pulses and ESD damage.



Circuit board layout and protection device placement

Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the device as close to the input terminal or connector as possible.
- 2. Minimize the path length between the device and the protected line.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protected conductors in parallel with unprotected conductors.
- 5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Use ground planes whenever possible. For multilayer PCBs, use ground vias.

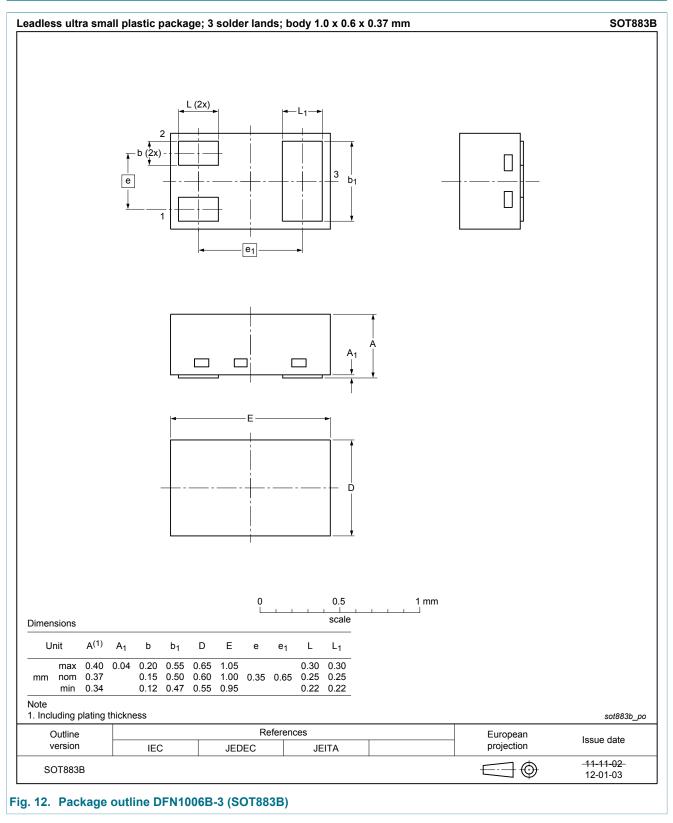
11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline



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13. Soldering

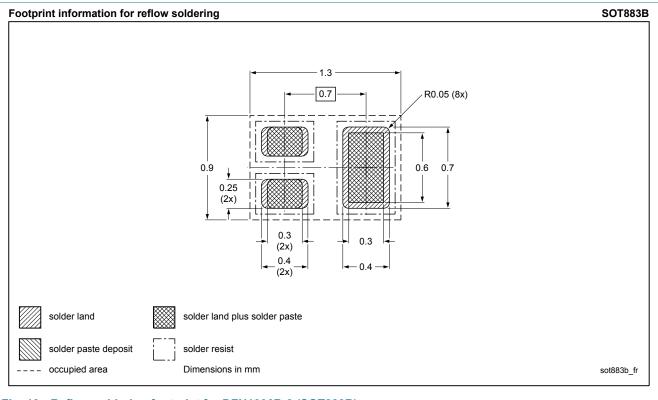


Fig. 13. Reflow soldering footprint for DFN1006B-3 (SOT883B)

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14. Revision history

Table 7. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PESD5V0V2BMB v.1	20150817	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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